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Hydrogen-related 3.8 eV UV luminescence in α -Ga₂O₃

D. Nicol^{1*}, Y. Oshima², J.W. Roberts³, L. Penman¹, D. Cameron¹, P.R. Chalker³, R.W. Martin¹, and F.C-P. Massabuau¹

¹ University of Strathclyde, Glasgow, G4 0NG, UK

² National Institute for Materials Science, Tsukuba, 3050044, Japan

³ School of Engineering, University of Liverpool, Liverpool, L69 3GH, UK

*E-mail: david.nicol@strath.ac.uk

Abstract

Temperature-dependent photoluminescence was used to investigate the impact of H on the optical properties of α -Ga₂O₃ films grown by halide phase vapor epitaxy. An additional UV luminescence line centered at 3.8 eV is observed at low temperatures and strongly correlates with the concentration of H in the films. This luminescence line is assigned to donor-acceptor-pair recombination involving an H-related shallow donor and H-decorated Ga vacancy (V_{Ga}-nH) as the acceptor, where n = 1,2,3. Previous reports have already suggested the impact of H on the electrical properties of Ga₂O₃, and our present shows its clear impact on the optical properties of α -Ga₂O₃.

Key words: Gallium Oxide, Temperature dependent, Hydrogen, Photoluminescence, Ultraviolet

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Gallium oxide (Ga_2O_3) is an emerging wide bandgap semiconductor with promising applications in power electronics and solar-blind photodetectors [1]. Ga_2O_3 is a polymorphic compound, with known phases labelled as α , β , δ , γ , and κ . Most attention has been dedicated to the thermodynamically stable monoclinic β -phase. However the rhombohedral α -phase of Ga_2O_3 exhibits many advantages over the other phases of Ga_2O_3 . Notably it exhibits the highest bandgap (*ca* 5.1-5.3 eV) amongst all phases [2] [3] [4] [5], which should result in a higher breakdown electric field value of 9.5 MV/cm compared to 8 MV/cm for β - Ga_2O_3 [6, 7], and offers interesting prospects for bandgap engineering through alloying with several isomorphous sesquioxides such as Al_2O_3 [8], In_2O_3 [9], Fe_2O_3 [10], or Ti_2O_3 [11]. Thus far, most of the attention of α - Ga_2O_3 research has been focused on material growth, leaving a gap in the knowledge of the properties of defects in the material. To improve the efficiency and reliability of Ga_2O_3 -based devices, it is however crucial to understand the influence of defects on the electrical and optical properties of α - Ga_2O_3 .

Photoluminescence (PL) is a well-established method for investigating the influence of defects on the optical properties of semiconductors [12]. PL studies on α - Ga_2O_3 remain relatively scarce compared to the other polymorphs. While this comes perhaps as a surprising result owing to the different crystal structures, several studies have reported no notable difference in the luminescence properties of α - and β - Ga_2O_3 [13] [14] [15]. Furthermore deep level transient and optical deep level transient spectroscopy studies of α - Ga_2O_3 and β - Ga_2O_3 also showed the two polymorphs exhibited a similar distribution of defect energy levels within the bandgap [16]. Therefore it seems reasonable in the first instance to refer to literature on PL of β - Ga_2O_3 to initiate a review on luminescence of α - Ga_2O_3 .

Typically β - Ga_2O_3 exhibits luminescence in the UV (3.2-3.6 eV) [17] [18] [19], blue (2.8-3.0 eV) [17] [20], and green (2.5 eV) [21] spectral regions, with luminescence in the red (1.7-1.9 eV) also reported [22] [23] [24]. Two UV lines have been assigned to intrinsic origins, with experimental and theoretical calculations attributing the luminescence to the recombination of free electrons with self-trapped holes (STH) [18] [25] [26]. However, Onuma *et al* suggested that the UV luminescence was composed of not only the recombination of STH and free electrons, but also had a contribution from donor-acceptor pair (DAP) recombination involving Si as a shallow donor with potential acceptors being Ga vacancies (V_{Ga}), substitutional Mg (Mg_{Ga}), substitutional N (N_{O}), and O-Ga divacancies ($V_{\text{O}}-V_{\text{Ga}}$) [17]. The blue luminescence is typically associated with DAP recombination involving a host of intrinsic defects with V_{O} , V_{Ga} , $V_{\text{O}}-V_{\text{Ga}}$, Mg_{Ga} and Ga interstitials (Ga_i) suggested as possible donors and acceptors [27] [28]. The green luminescence line is less studied with attribution thus far being to DAP recombination involving a range of defects including O_i and V_{Ga} [22] [29]. Finally, red luminescence has been linked to H or N impurities [23] [30] as well as reported sharp red luminescence lines attributed to the incorporation of Cr^{3+} ions [24].

H is a common yet elusive impurity in Ga_2O_3 , and the scarce reports have shown it can have dramatic impact on the properties of the material, such as controlling n- and p-type conductivity in β - Ga_2O_3 [31], as well as having an adverse effect on photocurrent [32]. H is predicted to act as a shallow donor, occupying either interstitial (H_i) or substitutional sites (H_{O}), and the low formation energy in both configurations suggests that it will be easily incorporated into the crystal lattice [33] [34]. Furthermore, the low migration barrier means we can expect H to diffuse in the lattice and interact with other defects such as V_{Ga} , where the vacancy has 4 dangling bonds which can readily accept the H and form complex $V_{\text{Ga}}\text{-nH}$ defects, where n is the number of H atoms in the complex [33]. Theory predicts that formation of $V_{\text{Ga}}\text{-nH}$ complexes in β - Ga_2O_3 is indeed more energetically favorable than that of the isolated V_{Ga} [35]. The state of the art suggests that H in $V_{\text{Ga}}\text{-nH}$ is strongly bound, so much so that work from Wei *et al* calculated theoretically predicted that temperatures in excess of 1000 K are required to dissociate the complex [36]. The influence of $V_{\text{Ga}}\text{-nH}$ on the electrical properties of Ga_2O_3 has been studied by Islam *et al* who demonstrated that by controlling the H incorporation in the crystal, the conductivity of the material was switched from n-type (when $n = 4$) to p-type ($n = 1, 2, 3$) [31].

As the impact of H on the electrical properties has become more established, there is a gap in the literature regarding the impact of H on the luminescence properties of the material. Jiang *et al* studied

the effect of H₂ plasma treatment on the electrical and optical properties of β-Ga₂O₃ films, and observed a decrease in the luminescence of samples exposed to H₂ plasma [37]. Huynh *et al* investigated H-doped β-Ga₂O₃ films by cathodoluminescence and reported the emergence of a red luminescence band centered at 1.9 eV after the film was exposed to H₂ plasma treatment [23]. In the present paper, we employ temperature-dependent PL to study the optical properties of α-Ga₂O₃ films with grown by halide vapor phase epitaxy (HVPE) containing variations of H and Cl concentrations, where the variation stems from a variation in gas partial pressures of GaCl_x and H₂ used during the growth process to stimulate rapid growth.

The α-Ga₂O₃ films were grown on *c*-plane sapphire by halide vapor phase epitaxy (HVPE) in a lab-made quartz reactor at 520°C under atmospheric pressure. O₂ (> 99.99995% pure) and GaCl were used as the precursors. The GaCl was synthesized by a chemical reaction of metal Ga (> 99.99999% pure) and HCl gas (> 99.999% pure) upstream in the reactor at 570°C. Additional HCl gas was also supplied to enable rapid growth [38] N₂ (dew point < -110°C) was used as the carrier gas. The growth conditions are summarized in Table 1, with P₀(X) being the supply partial pressure of gas X. The films were grown in two steps except for sample A. Samples B-D were grown relatively slowly at the first step, and the growth rate was increased at the second step by increasing the partial pressure of GaCl_x and H₂ where H₂ was produced by the chemical reaction of Ga and HCl in the reactor yielding different concentrations of H and Cl, as measured by secondary ion mass spectrometry (SIMS) as reported in Table 1. Here we note that C, N, Si, and S levels were measured but the concentrations were below the SIMS detection limit. All the films had a thickness in the range 3.5-3.8 μm. The samples were also analysed by X-ray diffraction (XRD), showing excellent phases purity (Figure 1S), and the broadening of the symmetric and asymmetric reflections reported in Table 1.

Sample	A	B	C	D
P ₀ (GaCl) (kPa)	0.125	0.125/0.25	0.125/0.5	0.125/1.0
P ₀ (H ₂)(kPa)	0.063	0.063/0.125	0.063/0.25	0.063/0.5
P ₀ (O ₂) (kPa)	1.25	1.25/3.125		
P ₀ (HCl) (kPa)	0.125	0.125/1.25		
Growth rate (μm/h)	11.9	11.9/34.1	11.9/73.4	11.9/116
Thickness (μm)	3.8	0.4/3.4	0.4/3.2	0.4/3.1
[H] (cm ⁻³)	< 6×10 ¹⁶	1.1×10 ¹⁷	1.5×10 ¹⁷	2.8×10 ¹⁷
[Cl] (cm ⁻³)	1×10 ¹⁶	1.8×10 ¹⁷	4.1×10 ¹⁷	1.4×10 ¹⁸
Tilt 0006 (arcsec)	-	135	359	103
Twist 10-12 (arcsec)	-	1820	1442	1361

Table 1 Summary of the growth conditions, and impurity concentration for the sample set

The optical properties of the films were evaluated using temperature-dependent PL measurements between 9 K and 290 K. A Photon Systems 224 nm HeAg pulsed laser was used as an excitation source. The luminescence from the samples was collected by a McPherson 207 monochromator with a 300 lines.mm⁻¹ diffraction grating and the light was detected by an Andor Technology CCD camera cooled to -50 °C. A 280 nm low-pass filter was positioned at the entrance of the spectrometer to remove the laser lines from the collected signal. This filter was replaced by a 470 nm low-pass filter to assess the presence of 2nd order diffraction of in the signal.

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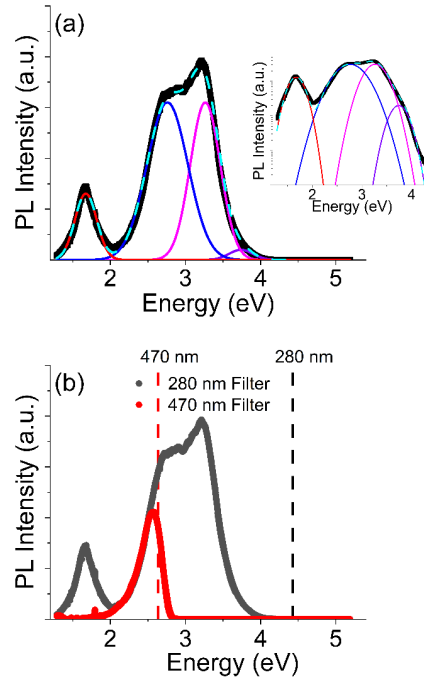


Figure 1(a) 290 K PL spectrum of sample C where the H concentration ($[H] = 1.5 \times 10^{17} \text{ cm}^{-3}$). Inset shows the PL spectrum of sample of sample C measured at 290 K in log scale highlighting the presence of the 3.8 eV peak (b) 290 K PL spectrum of sample C ($[H] = 1.5 \times 10^{17} \text{ cm}^{-3}$) with 280 nm filter (black) and 470 nm filter (red)

Figure 1(a) shows the typical 290 K spectrum of sample C. The PL spectra exhibit broad emission bands centered at 3.3 eV (UV), 2.7 eV (blue) and 1.6 eV (red) in close agreement with the literature [17] [18] [24]. Furthermore, we can distinguish an additional low intensity luminescence centered at 3.8 eV in the spectra in log scale (inset Fig 1(a)) – as will be discussed later, that luminescence becomes more pronounced at low temperature. This luminescence line has rarely been observed in the literature [30] [39] [14] and as of yet there has been no assignment of its origin.

The origin of the red luminescence line centered at 1.6 eV, as previously mentioned, has been typically associated with H or N impurities [23] [30]. Therefore, we paid particular attention to the red luminescence and how it varied depending on the H concentration of our films. However, due to the high intensity and position of the 3.3 eV UV line the possibility of 2nd order diffraction having an impact on the emission spectra must be considered. To address this, we inserted a 470 nm filter to remove the UV luminescence, which resulted in the removal of the red luminescence from the spectra, shown in figure 1(b). Therefore, for the samples analyzed in this paper, the red emission is determined to be that of 2nd order diffraction of the UV and will not be shown in the luminescence spectra in the later figures.

By analogy to $\beta\text{-Ga}_2\text{O}_3$, UV emission is typically attributed to the recombination of free electrons with STH. One of the reasons for the generation of these STH lies in the composition of the valence band

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for which the upper state is mainly made up of O $2p$ orbitals which have characteristics such as small dispersion and large effective masses [40]. The associated holes, with large effective mass, become localized at O sites in the crystal lattice. In β -Ga₂O₃ there are three non-equivalent O sites, two of which have trigonal coordination and one with tetrahedral coordination [41]. According to first principle calculations, the holes tend to localize on the trigonally coordinated sites meaning there are two possible sites for the STHs in β -Ga₂O₃ [41], which is reflected in PL with two bands resolved in the UV region [22]. However, α -Ga₂O₃ has only one type of O site [41]. Therefore it may be expected that only one luminescence band in the UV region may be attributed to recombination of free electrons and STH, ruling out the assignment of the 3.8 eV line as STH-related.

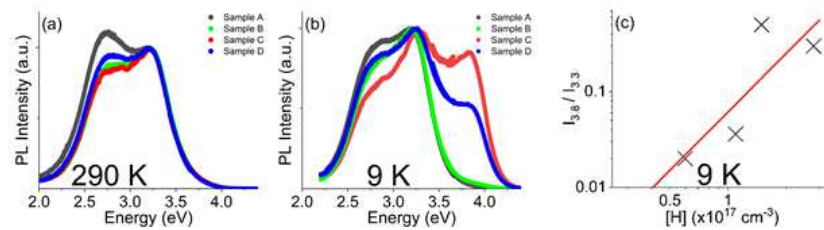


Figure 2. PL spectra of samples A, B, C and D measured at (a) 290 K (b) 9 K. (c) Illustrates the correlation between the integrated intensity of the 3.8 eV luminescence line and H concentrations of the samples

Figure 2(a) shows the PL spectra of all samples measured at 290 K. Apart from the small variation in blue line intensity, all of the 290 K PL spectra were identical. Strong variation across the samples appeared when the temperature was decreased to 9 K, as shown in figure 2(b). The PL spectra of sample C with the 480 nm filter and full emission spectrum including red emission is shown in figure 2S and 3S, respectively. Figure 2(b) shows a clear enhancement of the 3.8 eV luminescence line with respect to the 290 K measurements. To assess the impact of temperature on the luminescence lines, we looked at the ratio of the integrated intensities of each line measured at 9 K and 290 K. We observe a disproportionate enhancement of the integrated intensity of the 3.8 eV luminescence line of samples C and D which increase by a factor of 18 and 15 respectively compared to samples A and B where for sample A there is no enhancement of the 3.8 eV luminescence line at 9 K and for B only increases by a factor of 2. From the SIMS measurements in shown in Table 1, it can be seen that samples C and D have a higher concentration of H and Cl. These impurities are incorporated into the films during the growth process where HCl was used, however $P_0(\text{HCl})$ is the same for samples B-D. Therefore, the additional HCl should not be the dominant case of the variation in $[\text{H}]$ and $[\text{Cl}]$. Rather, we expect GaCl₃ and H₂ were the impurity sources because their partial pressures were increased to increase the growth rate. Note that H₂ was produced by the chemical reaction at the Ga container upstream in the reactor ($\text{Ga} + \text{HCl} = \text{GaCl} + 1/2\text{H}_2$). H₂ was also produced by the following reaction $\text{GaCl} + 2\text{HCl} = \text{GaCl}_3 + \text{H}_2$. More details can be found in ref [38]. The variation of the 3.8 eV integrated emission at 9 K with impurity concentration is a strong indicator that this luminescence line is not associated with STH emission, as STH luminescence is assumed to be impurity independent [22]. From theoretical calculations, it is predicted that both H and Cl can act as shallow donors in Ga₂O₃ [33], which would explain the strong correlation of the integrated intensity with temperature.

In order to distinguish between whether H or Cl is responsible, we turn our attention to samples which were grown by plasma enhanced atomic layer deposition (PEALD) [42]. The PEALD growth process involves the use of triethylgallium $[\text{Ga}(\text{C}_2\text{H}_5)_3]$ as Ga precursor, Ar as purge gas, and O₂ as plasma source. No Cl is involved in the process, nor in the design of the reactor. The PL spectra of the PEALD samples were measured at 9 K, shown in figure 4S in the supplementary information. In this sample we observe similar emission properties of the 3.8 eV luminescence line in that we observe low, barely

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distinguishable emission at 290 K and then a strong increase in intensity at 9 K, which leads us to believe the 3.8 eV lines relates to H, and not Cl.

Therefore, we now turn our attention to the role of H in the samples. We observe a strong correlation between the ratio of the integrated intensity at 9 K of the luminescence lines centered at 3.3 eV and 3.8 eV where the integrated intensity ratio tends to increase with H concentration as shown in Figure 2(c). We note that the luminescence of sample C is stronger than sample D despite having a lower H concentration. Atomic force microscopy (AFM) and XRD were used to assess whether this variation luminescence could be due to sample quality. AFM data (figure 5S) shows that the surface morphology of these two samples are very similar, in terms of topography and roughness. XRD analysis (figure 1S) shows that the samples are all phase pure. We note that the main difference between samples C and D is that sample C exhibits a greater tilt (359 arcsecs) compared to sample D (103 arcsecs). While these are values are still low, the increased tilt indicates a slightly greater misorientation of the grains, leading a greater density of grain boundaries and dislocations in sample C which could have an (still not fully understood) effect on the luminescence. The 3.3 eV emission has already been attributed to STH which will be invariant of impurities. H incorporates into Ga₂O₃ either on interstitial (H_i) or substitutional (H_o) sites, with both exhibiting low formation energies [35]. Therefore both are likely to exist as shallow donors in Ga₂O₃. Previous work on Muonium, which has similar characteristics to H, suggested H is a shallow donor with a donor depth $15 < E_d < 30$ meV [43].

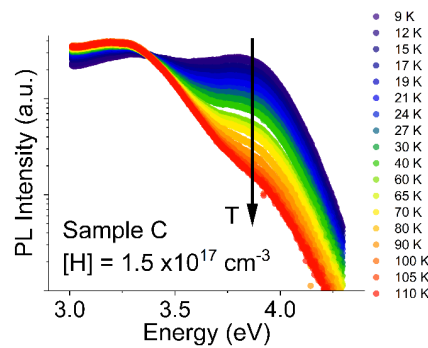


Figure 3 Temperature dependent luminescence of sample C measured between 9 K and 110 K

We investigated the temperature dependence of the 3.8 eV line, shown in figure 3. We can see that the intensity of the line increases dramatically as the temperature decreases below 100 K, while the 3.3 eV line is comparatively less affected by the temperature. Due to the strong overlap between the lines, it would be inaccurate to attempt to extract an activation energy for this line. However, such a temperature dependence is in line with an origin involving a shallow donor with E_d in the order of 10s meV.

To address the energy emission of 3.8 eV, we require a deep level acceptor to facilitate the recombination from the aforementioned H related donor. It is well established that it is difficult to identify with absolute certainty the defect involved in the recombination process via PL measurements, even more so in the case where broad, overlapping luminescence lines are involved such as those shown in Ga₂O₃. However, what we can establish is that there is a strong correlation between the H concentration of the thick films and the integrated intensity of the 3.8 eV luminescence line. It is therefore reasonable to suggest that H plays a significant role in the recombination process. As previously mentioned, the interaction of H and V_{Ga} leads to the formation of H-decorated V_{Ga} complexes (V_{Ga}-nH), where n is the number of H atoms involved in the complex defect, Polyakov *et al* identified a defect energy level positioned 1.3 eV above the valence band maximum [44]. We can tentatively improve on the precision of the number of H atoms

involved in the complex vacancy by revisiting the work by Islam *et al* which showed that the complex vacancy will be in the acceptor state when 1, 2, or 3 H atoms are bound to the V_{Ga} [31]. To assess the suitability of the V_{Ga} -nH related complex as the acceptor in our DAP recombination model, we use equation 1 to calculate the emission energy.

$$h\nu(DAP) = E_g - (E_a + E_d) + \frac{e^2}{4\pi\epsilon r} \quad (1)$$

Where E_g is the bandgap energy, E_a is the acceptor ionization energy, E_d is the donor ionization energy, the final term on the right of equation 1 represents the Coulomb interaction where e is the charge of an electron, ϵ is the low frequency dielectric constant and r is the separation of the donor and acceptor. As a first approximation, the distance r can be given as a function of donor concentration, N_D , given by equation 2

$$r = \sqrt[3]{\frac{3}{4\pi N_D}} \quad (2)$$

Yielding a donor-acceptor pair separation of 11 nm assuming the donor concentration is in the order of magnitude of the H concentration detected by the SIMS measurements shown in table 1. Using 10 as the relative permittivity of α -Ga₂O₃ [44], $E_d = 15$ -30 meV as the shallow donor ionization energy obtained from King *et al* [43] (in line with our observation of figure 3), E_a as 1.3 eV as obtained from Polyakov *et al* [44] and finally $E_g = 5.2$ eV from the transmittance measurements shown in figure 6S, we find a DAP emission energy of 3.9 eV which is in excellent agreement with our emission energy obtained experimentally. A schematic of the proposed DAP recombination process is shown in fig 4.

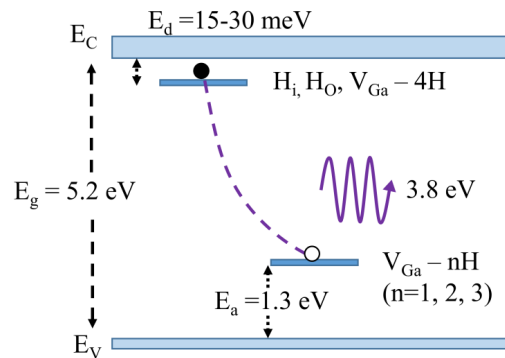


Figure 4 – Model for the 3.8 eV luminescence recombination mechanism. The purple dashed line represents donor acceptor pair recombination when $T < 110$ K.

The variation of the integrated intensity of the 3.8 eV line with H concentration, along with the identification of the V_{Ga} related complex 1.3 eV above the valence band by Polyakov *et al* leads us to believe there is strong evidence of H decorated V_{Ga} complex acts as an acceptor in our recombination model [44]. The low formation energy of H related donors, along with the low activation energy strongly favours the incorporation as H as a donor in either H_i , H_o , V_{Ga} -nH configuration [31] [35] [43]. However, due to the shallow donor depth, we cannot unequivocally rule out the role of a bound exciton. Further power dependent and time resolved luminescence studies will offer further insight into mechanisms involved in the 3.8 eV emission

In conclusion, we investigated the optical properties of α -Ga₂O₃ thick films with measureable variations of H and Cl concentrations by means of temperature-dependent PL. The study shows a significant enhancement of UV luminescence band at 3.8 eV at low temperatures, with a strong correlation with the H concentration of the samples. Sample A ($[H] < 6 \times 10^{16} \text{ cm}^{-3}$) exhibits barely distinguishable luminescence at 3.8 eV even at temperatures as low as 9 K. On the other hand, Samples C ($[H] = 1.5 \times 10^{17} \text{ cm}^{-3}$) and D ($[H] = 2.8 \times 10^{17} \text{ cm}^{-3}$) showed an enhancement in integrated intensity by a factor of 15 and 20, respectively. The strong temperature dependence of the 3.8 eV luminescence line with temperature, indicates the role of a shallow donor. Here, we tentatively ascribe the luminescence to DAP recombination where the donor is H related with possible candidates being H_i, H_O or V_{Ga}-4H, and the acceptor as V_{Ga}-nH where n = 1, 2, 3. This study indicates that even small changes in H content of less than 1 order of magnitude can have a significant on the UV luminescence properties.

Supplementary Material

See the supplementary material for a XRD ω -2 θ scans, PL spectra with 280 and 470 nm filter, PL spectra of PEALD samples measured at 290 K and 9 K, Topography maps obtained by AFM, and transmittance measurements obtained using UV-VIS spectroscopy.

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References

- [1] S. J. Pearton, J. Yang, P. Cary, F. Ren, J. Kim, M. Tadjer, M. Mastro, "A review of Gallium Oxide materials, processing, and devices," *Applied Physics Reviews*, vol. 5, no. 1, p. 011301, 2018.
- [2] D. Shinohara, S. Fujita, "Heteroepitaxy of Corundum-Structured α -Ga₂O₃ Thin Films on α -Al₂O₃ Substrates by Ultrasonic Mist Chemical Vapor Deposition," *Japanese Journal of Applied Physics*, vol. 47, no. 2008, p. 7311, 2008.
- [3] H. Sun, K. -H. Li, C. Torres Catanedo, S. Okur, G. Tompa, T. Salagaj, S. Lopatin, A. Genovese, X. Li, "HCl Flow-Induced Phase Change of α -, β -, and ϵ -Ga₂O₃ Films Grown by MOCVD," *Crystal Growth and Design*, vol. 2370, p. 18, 2018.
- [4] J. Roberts, P. Chalker, B. Ding, R. Oliver, J. Gibbon, L. Jones, V. Dhanak, L. Phillips, J. Major, F. P. Massabuau, "Low temperature growth and optical properties of α -Ga₂O₃ deposited on sapphire by plasma enhanced atomic layer deposition," *Journal of Crystal Growth*, vol. 528, p. 125254, 2019.
- [5] V. Wheeler, N. Nepal, D. Boris, S. Qadri, S. Nyakiti, L. Lang, A. Koehler, G. Foster, S. Walton, C. Eddy, D. Meyer, "Phase control of crystalline Ga₂O₃ films by plasma induced atomic layer deposition," *Chemistry of Materials*, vol. 32, no. 3, pp. 1140-1152, 2020.
- [6] E. Ahmadi, Y. Oshima, "Materials and Devices," *Journal of Applied Physics*, vol. 126, no. 16, p. 160901, 2019.
- [7] A. J. Green, J. Speck, G. Xing, P. Moens, F. Allerstam, K. Gumaelius, T. Neyer, A. Arias-Purdue, V. Mehotra, A. Kuramata, K. Sasaki, S. Watanabe, K. Koshhi, J. Blevins, O. Bierwagen, S. Krishnamoorthy, K. Leedy, A. A. Arehart, A. T. Neal, S. Mou, S. A. Ri, "β-Gallium oxide power electronics," *APL Materials*, vol. 10, p. 029201, 2022.
- [8] R. Jinno, C. S. Chang, T. Onuma, Y. Cho, S. Ho, D. Rowe, M. C. Cao, K. Lee, V. Protasenko, D. G. Schlom, D. A. Muller, H. G. Xing, D. Jena, "Crystal orientation dictated epitaxy of ultrawide-bandgap 5.4- to 8.6-eV α -(AlGa)₂O₃ on m-plane sapphire," *Science Advances*, vol. 7, p. eabd5891, 2021.

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PLEASE CITE THIS ARTICLE AS DOI: 10.1063/5.0135103

- [9] K. Kaneko, K. Uno, R. Jinno, S. Fujita, "Prospects for phase engineering of semi-stable Ga₂O₃ semiconductor thin films using mist chemical vapor deposition," *Journal of Applied Physics*, vol. 131, p. 090902, 2022.
- [10] S. Fujita, K. Kaneko, "Epitaxial growth of corundum-structured wide bandgap III-oxide semiconductor thin films," *Journal of Crystal Growth*, vol. 32, p. 588, 2014.
- [11] A. Barthel, J. Roberts, M. Napari, M. Fentrup, T. Huq, A. Kovacs, R. Oliver, P. Chalker, T. Sajavaara, F. Massabuau, "Ti Alloyed α -Ga₂O₃: Route towards Wide Band Gap Engineering," *Micromachines*, vol. 11, p. 1128, 2020.
- [12] M. A. Reshnikov, "Luminescence from point defects in wide-bandgap, direct-gap semiconductors," in *Characterisation and Control of Defects in Semiconductors*, London, The Institution of Engineering and Technology, 2019, pp. 45-89.
- [13] L. Ghadbeigi, J. Cooke, G. T. Dang, T. Kawaharamura, T. Yasuka, R. Sun, P. Ranga, S. Krishnamoorthy, M. Scarpulla, B. Sensale-Rodriguez, "Optical Characterization of Gallium Oxide α and β Polymorph Thin-Films Grown on c -Plane Sapphire," *Journal of Electronic Materials*, vol. 50, no. 6, pp. 2990-2998, 2021.
- [14] S. Shapenkov, O. Vyvenko, E. Ubiivok, O. Medvedev, G. Varygin, A. Chikiryaka, A. Pechnikov, M. Scheglov, S. Shepenkov, V. Nikolaev, "HVPE growth of α - and ϵ -Ga₂O₃ on patterned sapphire substrates," *Physica status solidi (a)*, vol. 217, no. 14, p. 19200892, 2020.
- [15] A. Polyakov, N. Smirnov, I. Scherbachev, E. Yamikov, V. Nikolaev, S. Stepanov, A. Pechnikov, A. Chernykh, K. Shcherbachev, A. Shikoh, A. Kochkova, A. Vasilev, S. Pearton, "Deep trap spectra of Sn-doped α -Ga₂O₃ grown by halide vapor phase epitaxy on sapphire," *APL Materials*, vol. 2019, p. 051103, 2019.
- [16] Z. Wang, X. Chen, F. F. Ren, S. Gu, J. Ye, "Deep-level defects in Ga₂O₃," *Journal of Physics D: Applied Physics*, vol. 54, p. 043002, 2020.
- [17] T. Onuma, S. Fukioka, T. Yamaguchi, M. Sasaki, T. Masui, T. Honda, "Correlation between blue luminescence intensity and resistivity in β -Ga₂O₃ single crystals," *Applied Physics Letters*, vol. 103, p. 041910, 2013.
- [18] Y. Wang, P. T. Dickens, J. B. Varley, X. Ni, E. Lotubai, S. Sprawls, "Incident wavelength and polarization dependence of spectral shifts in β -Ga₂O₃ UV photoluminescence," *Scientific Reports*, vol. 8, no. 1, pp. 1-7, 2018.
- [19] Y. Berencen, Y. Xie, M. Wang, S. Pruncal, L. Rebohle, S. Zhou, "Structural and optical properties of pulsed-laser deposited crystalline β -Ga₂O₃ thin films on silicon," *Semiconductor Science and Technology*, vol. 34, no. 3, p. 035001, 2019.
- [20] O. M. Burdon, B. O. Bordun, I. Y. Kukharsky, I. I. Medvid,, "Photoluminescence Properties of β -Ga₂O₃ Thin Films Produced by Ion-Plasma Sputtering," *Journal of Applied Spectroscopy*, vol. 84, no. 1, pp. 46-51, 2017.
- [21] E. G. Villora, M. Yamaga, T. Inoue, G. Yabasi, Y. Masui, T. Sugawara, T. Fukuda, "Optical Spectroscopy Study on β -Ga₂O₃," *Japanese journal of applied Physics*, vol. 41, no. 6A, p. L622, 2002.
- [22] Q. D. Ho, T. Fraunheim, P. Deak, "Origin of photoluminescence in β -Ga₂O₃," *Physical Review B*, vol. 103, no. 4, p. 041910, 2013.
- [23] T. Huynh, E. Chikoidze, C. Irvine, M. Zakria, Y. Dumont, F. Teherani, E. Sandana, P. Bove, D. Rogers, M. Phillips, C. Ton-That, "Red luminescence in H-doped β -Ga₂O₃," *Physical Review Materials*, vol. 97, p. 115163, 2018.
- [24] N. Gunasekar, H. MacIntyre, S. Subashchandran, P. Edwards, R. Martin, K. Daivasigamani, K. Sasaki, A. Kuramata, "Origin of Red Emission in β -Ga₂O₃ Analyzed by Cathodoluminescence and Photoluminescence Spectroscopy," *Physica Status Solidi B*, vol. 258, p. 2000465, 2021.
- [25] J.B. Varley, A. Janotti, C. Franchini, C. G. Van de Walle, "Role of self-trapping in luminescence and p-type conductivity of wide-band-gap oxides," *Physical Review B*, vol.

This is the author's peer reviewed, accepted manuscript. However, the online version of record will be different from this version once it has been copyedited and typeset.

PLEASE CITE THIS ARTICLE AS DOI: 10.1063/5.0135103

- 85, p. 081109(R), 2012.
- [26] Q. D. Ho, T. Fraunheim, P. Deak, "Origin of photoluminescence in β -Ga₂O₃," *Physical Review B*, vol. 97, p. 115163, 2018.
- [27] L. Binet, D. Gourier, "ORIGIN OF THE BLUE LUMINESCENCE OF β -Ga₂O₃," *Journal of Physics and Chemistry*, vol. 59, pp. 1241-1249, 1998.
- [28] Y. Nie, S. Joao, S. Li, H. Lu, S. Liu, S. Yang, D. Wang, S. Gao, J. Wang, Y. Li, "Modulating the blue and green luminescence in the β -Ga₂O₃ films," *Journal of Alloys and Compounds*, vol. 900, p. 163341, 2022.
- [29] Y. Berenchen, Y. Xie, M. Wang, S. Prucnal, L. Rebohle, S. Zhou, "Structural and optical properties of pulsed-laser deposited crystalline β -Ga₂O₃ thin films on silicon," *Semiconductor Science and Technology*, vol. 34, p. 035001, 2019.
- [30] G. Pozina, M. Forsberg, M. A. Kaliteevski, C. Hemmingsson, "Emission properties of Ga₂O₃ nano-flakes: effect of excitation density," *Scientific Reports*, vol. 7, no. 1, pp. 1-8, 2017.
- [31] M. M. Islam, M. O Liedke, D. Winarski, M. Butterling, A. Wagner, P. Hoseman, Y. Wang, B. Uberuaga, F. A. Selim, "Chemical manipulation of hydrogen induced high p-type and n-type conductivity in Ga₂O₃," *Scientific reports*, vol. 10, no. 1, pp. 1-10, 2020.
- [32] J. Moloney, O. Tesh, M. Singh, J. W. Roberts, J. C. Jarman, C. L. Lee, T. N. Huq, J. Bister, S. Karboyan, M. Kuball, P. R. Chalker, R. A. Oliver, F. C-P. Massabuau, "Atomic layer deposited α -Ga₂O₃ solar-blind photodetectors," *Journal of Physics D: Applied Physics*, vol. 52, p. 475101, 2019.
- [33] J. B. Varley, J. R. Weber, A. Janotti, C. G. Van de Walle, "Oxygen vacancies and donor impurities in β -Ga₂O₃," *Applied Physics Letters*, vol. 97, no. 14, p. 142106, 2010.
- [34] M. J. Tadjer, J. L. Lyons, N. Nepal, J. A. Freitas Jr, A. D. Koehler, G. M. Foster, "Theory and Characterization of Doping and Defects in β -Ga₂O₃," *ECS Journal of Solid State Science and Technology*, vol. 8, p. Q3187, 2019.
- [35] J. B. Varley, "First-Principles Calculations 2- Doping and Defects in Ga₂O₃," in *Gallium Oxide - Materials Properties, Crystal Growth, and Devices*, Livermore, Springer, 2020, pp. 329-348.
- [36] Y. Wei, X. Li, J. Yang, C. Liu, J. Zhao, Y. Liu, S. Dong, "Interaction between hydrogen and gallium vacancies in β -Ga₂O₃," *Scientific Reports*, vol. 8, pp. 1-8, 2018.
- [37] Q. Jiang, J. Meng, Y. Shi, Z. Yin, J. Chen, J. Zhang, J. Wu, X. Xhang, "Electrical and optical properties of hydrogen plasma treated β -Ga₂O₃ thin films," *Journal of Semiconductors*, vol. 43, pp. 1-6, 2022.
- [38] Y. Oshima, K. Kawara, T. Oshima, Okigawa, Shinohe, "Rapid growth of α -Ga₂O₃ by HCl-boosted halide vapor phase epitaxy and effect of precursor supply conditions on crystal properties," *Semiconductor Science and Technology*, vol. 35, p. 055022, 2020.
- [39] X. T. Zhou, F. Heigl, J. Y. P. Ko, M. W. Murphy, J. G. Zhou, T. Reiger, R. I. R. Blyth, T. K. Sham, "Origin of luminescence from Ga₂O₃ nanostructures studied using x-ray absorption and luminescence spectroscopy," *Physical Review B*, vol. 75, p. 125303, 2007.
- [40] B. E. Kananen, N. C. Giles, L. E. Halliburton, G. K. Foundos, K. B. Chang, K. T. Stevens, "Self-trapped holes in β -Ga₂O₃ crystals," *Journal of Applied Physics*, vol. 122, no. 21, p. 215703, 2017.
- [41] T. Gake, Y. Kumagai, F. Oba, "First principle study of self-trapped holes and acceptor impurities in Ga₂O₃ polymorphs," *Physical Review Materials*, vol. 3, no. 4, p. 044603, 2019.
- [42] F. C.-P. Massabuau, J. W. Roberts, D. Nicol, P. R. Edwards, M. McLelland, G. L. Dallas, D. A. Hunter, E. A. Nicolson, J. C. Jarman, A. Kovacs, R. W. Martin, R. A. Oliver, P. R. Chalker, "Progress in atomic layer deposited α -Ga₂O₃ materials and solar blind detectors," *Proceedings of SPIE*, vol. 11687, p. 116870Q, 2021.

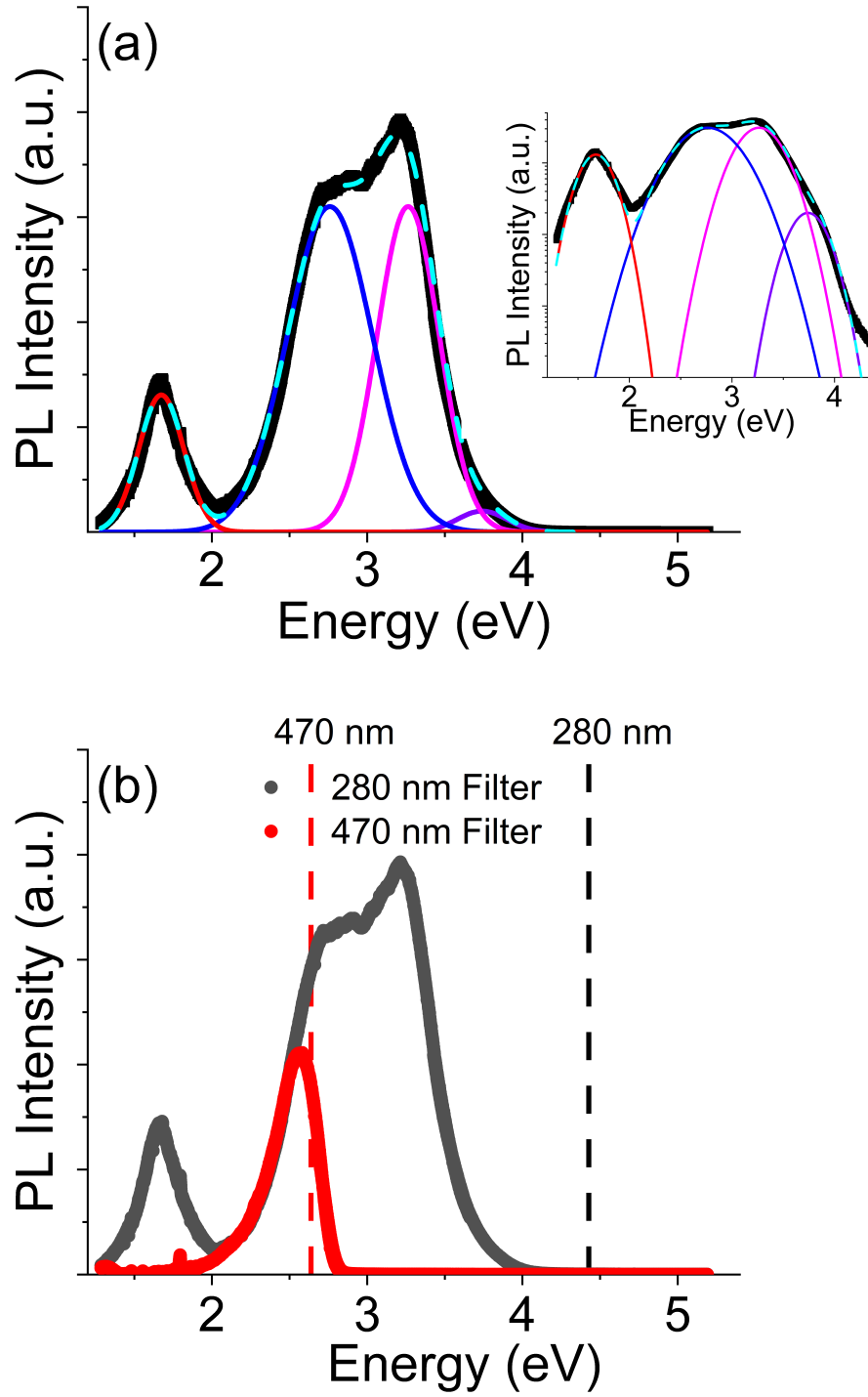
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PLEASE CITE THIS ARTICLE AS DOI: 10.1063/5.0135103

- [43] P. D. C. King, I. McKenzie, T. D. Veal, "Observation of shallow donor muonium in Ga₂O₃: Evidence for hydrogen-induced conductivity," *Applied Physics Letters*, vol. 96, no. 2, p. 062110, 2010.
- [44] A. Polyakov, V. I. Nikolaev, E. B. Yakimov, F. Ren, S. J. Pearton, J. Kim, "Deep level defect states in β -, α -, and ϵ -Ga₂O₃ crystals and films: Impact on device performance," *Journal of Vacuum Science & Technology A*, vol. 40, p. 020804, 2022.
- [45] C. Huang, H. Zhang, H. Sun, "Ultraviolet optoelectronic devices based on AlGaN-SiC platform: Towards monolithic photonics integration system," *Nano Energy*, vol. 77, p. 105149, 2020.
- [46] H. Playford, A. Hannon, A. Barney, E. Barney, R. Walton, "Structures of uncharacterised polymorphs of Gallium Oxide from total neutron diffraction," *Chemistry- A European Journal*, vol. 19, no. 8, pp. 2803-2813, 2013.
- [47] M. A. Reshnikov, "Measurement and analysis of photoluminescence of GaN," *Journal of Applied Physics*, vol. 129, p. 121101, 2021.
- [48] L. Dong, R. Jia, B. Xin, B. Peng, Y. Zhang, "Effects of oxygen vacancies on the structural and optical properties of β -Ga₂O₃," *Scientific Reports*, vol. 7, p. 40160, 2017.
- [49] "Origin of Red Emission in β -Ga₂O₃ Analyzed by Cathodoluminescence and Photoluminescence Spectroscopy," *G. Naresh-Kumar, H. MacIntyre, S. Subashchandra, P. R. Edwards, R. W. Martin, K. Daivasigamani, K. Sasaki, A. Kuramata*, vol. 258, p. 2000465, 2020.
- [50] H. Zhou, J. Zhang, C. Zhang, Q. Feng, Z. Zhao, P. Ma, Y. Hao, "A review of the most recent progresses of state of the art Gallium Oxide devices," *Journal of Semiconductors*, vol. 40, no. 1, p. 011803, 2019.
- [51] H. Zhang, C. Huang, K. Song, H. Yu, C. Xing, D. Wang, "Compositionally grade III-nitride alloys: Building blocks for efficient ultraviolet optoelectronic and power electronics," *Reports in Progress in Physics*, vol. 84, p. 044401, 2021.
- [52] M. E. Ingebrigsten, A. Yu. Kuznetsov, B. G. Svenson, G. Alfieri, A. Mihaila, U. Badstubner, A. Perron, L. Vines, J. B. Varley, "Impact of proton irradiation on conductivity and deep level defects in β -Ga₂O₃," *APL Materials*, vol. 7, p. 022510, 2019.
- [53] A. Q. Huang, "New Unipolar Switching Power Device Figure of Merit," *IEEE Electron Device Letters*, vol. 25, no. 5, p. 298, 2004.
- [54] R. Roy, V. Hill, E. Osborn, "Polymorphism of Gallium Oxide and the system Ga₂O₃-H₂O," *Journal of the American Chemical Society*, vol. 74, no. 3, p. 719, 1952.
- [55] Y. K. Frodason, K. M. Johansen, L. Vines, J. B. Varley, "Self-trapped hole and impurity-related broad luminescence in β -Ga₂O₃," *Journal of Applied Physics*, vol. 127, p. 075701, 2020.
- [56] S. Cho, J. Lee, I. Y. Park., S. Kim, "Temperature Dependence of Photoluminescence of α -Ga₂O₃ Powders," *Japanese Journal of Applied Physics*, vol. 41, p. 5237, 2002.
- [57] Y. Shi, D. Huang, F. Ling, Q. Tian, L. Liao, M. R. Phillips, C. Ton-That, "Correlation between small polaron tunneling relaxation and donor ionisation in Ga₂O₃," *Applied Physics Letters*, vol. 120, p. 172105, 2022.
- [58] Y. P. Song, H. Z. Zhang, C. Lin, Y. W. Zhu, G. H. Li, F. H. Yang, D. P. Yu, "Luminescence emission originating from nitrogen doping of β -Ga₂O₃ nanowires," *Physical Review B*, vol. 69, p. 075304, 2004.

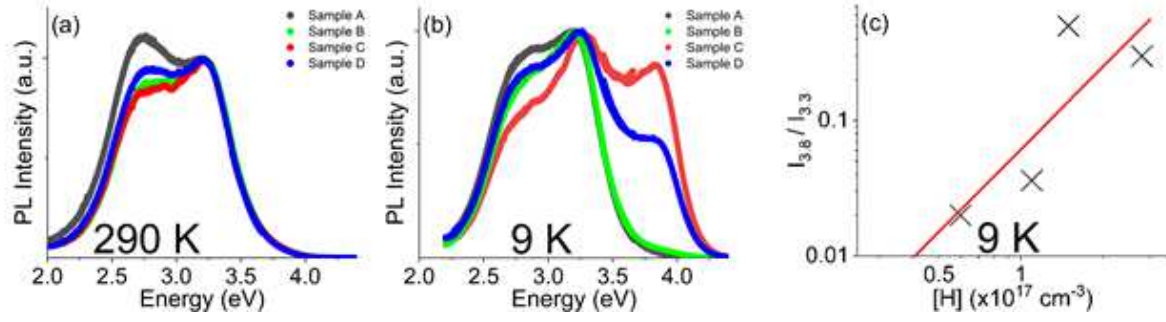
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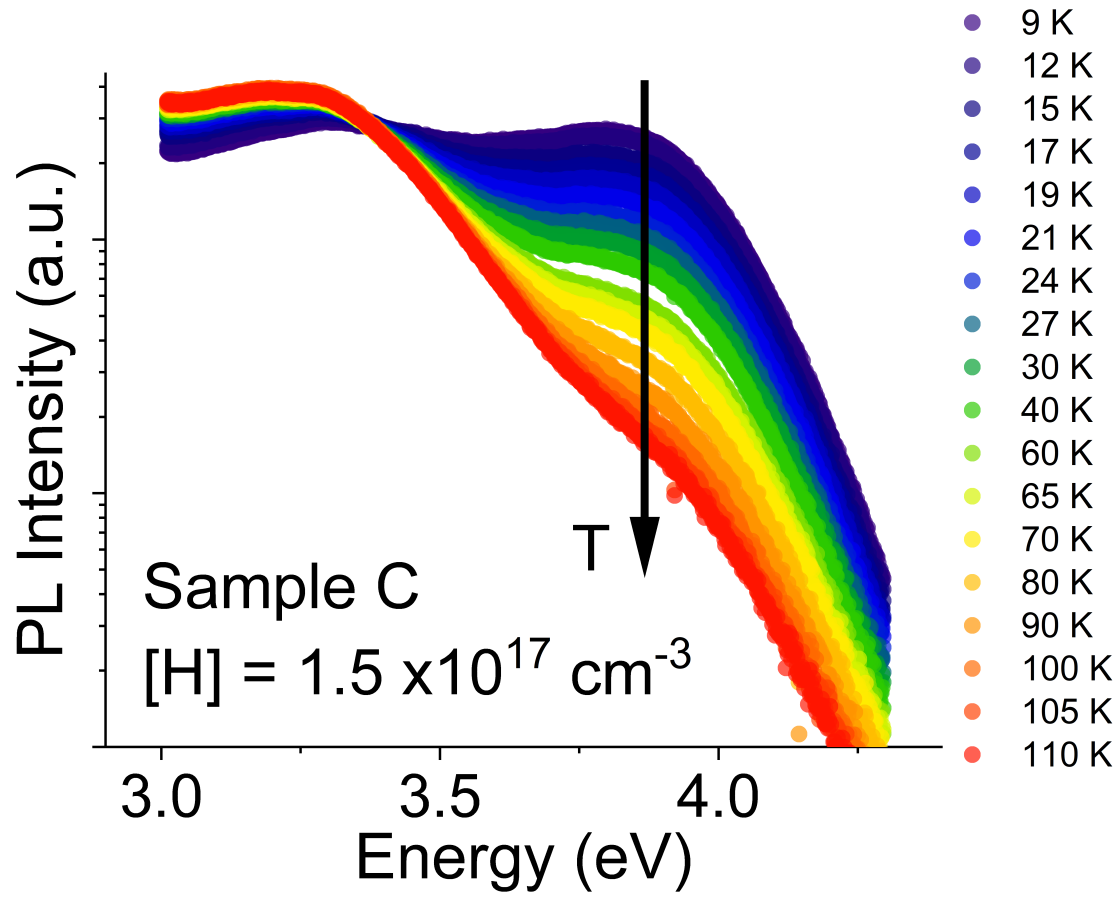
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